



M74HCT125

QUAD BUS BUFFER (3-STATE)

- HIGH SPEED:
 $t_{PD} = 13\text{ns}$ (TYP.) at $V_{CC} = 4.5\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS :
 $V_{IH} = 2\text{V}$ (MIN.) $V_{IL} = 0.8\text{V}$ (MAX)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 6\text{mA}$ (MIN)
- PIN AND FUNCTION COMPATIBLE WITH
 74 SERIES 125



ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HCT125B1R	
SOP	M74HCT125M1R	M74HCT125RM13TR
TSSOP		M74HCT125TTR

DESCRIPTION

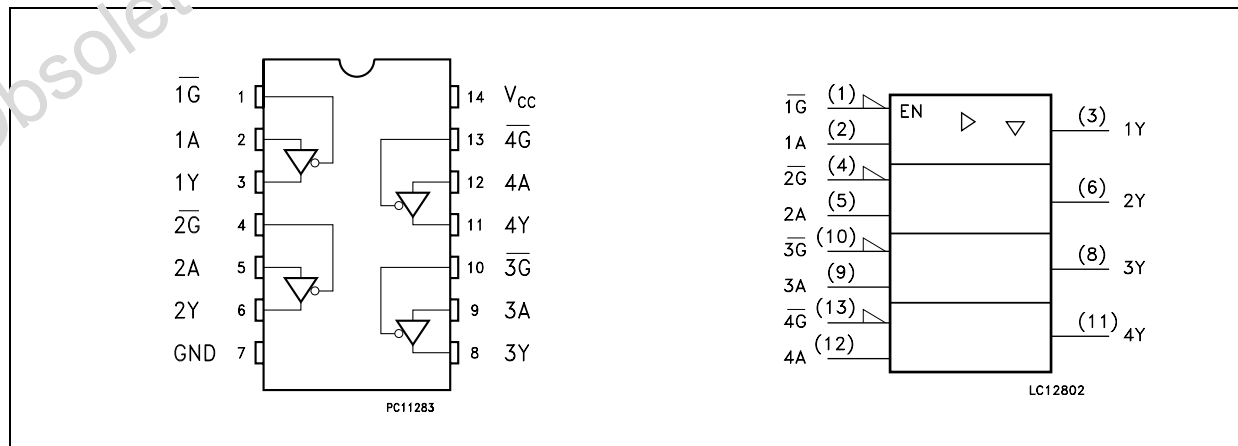
The M74HCT125 is an high speed CMOS QUAD BUFFER (3-STATE) fabricated with silicon gate C²MOS technology.

The device requires the 3-STATE control input \overline{G} to be set high to place the output in to the high impedance state.

The M74HCT125 is designed to directly interface HSC²MOS systems with TTL and NMOS components.

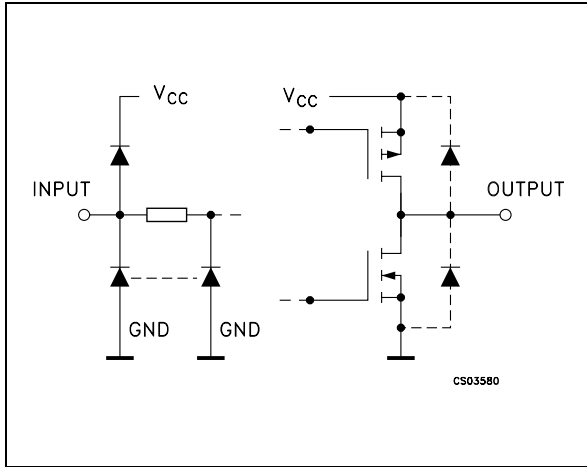
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



M74HCT125

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	$\overline{1G}$ TO $\overline{4G}$	Output Enable Input
2, 5, 9, 12	1A TO 4A	Data Inputs
3, 6, 8, 11	1Y TO 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	\overline{G}	Y
X	H	Z
L	L	L
H	L	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 35	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 70	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.5 to 5.5	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
t _r , t _f	Input Rise and Fall Time (V _{CC} = 4.5 to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V _{OH}	High Level Output Voltage	4.5	I _O = -20 μA	4.4	4.5		4.4		4.4		V
			I _O = -6.0 mA	4.18	4.31		4.13		4.10		
V _{OL}	Low Level Output Voltage	4.5	I _O = 20 μA		0.0	0.1		0.1		0.1	V
			I _O = 6.0 mA		0.17	0.26		0.33		0.40	
I _I	Input Leakage Current	5.5	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{OZ}	High Impedance Output Leakage Current	5.5	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			± 0.5		± 5		± 10	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			4		40		80	μA
Δ I _{CC}	Additional Worst Case Supply Current	5.5	Per Input pin V _I = 0.5V or V _I = 2.4V Other Inputs at V _{CC} or GND I _O = 0			2.0		2.9		3.0	mA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6ns)

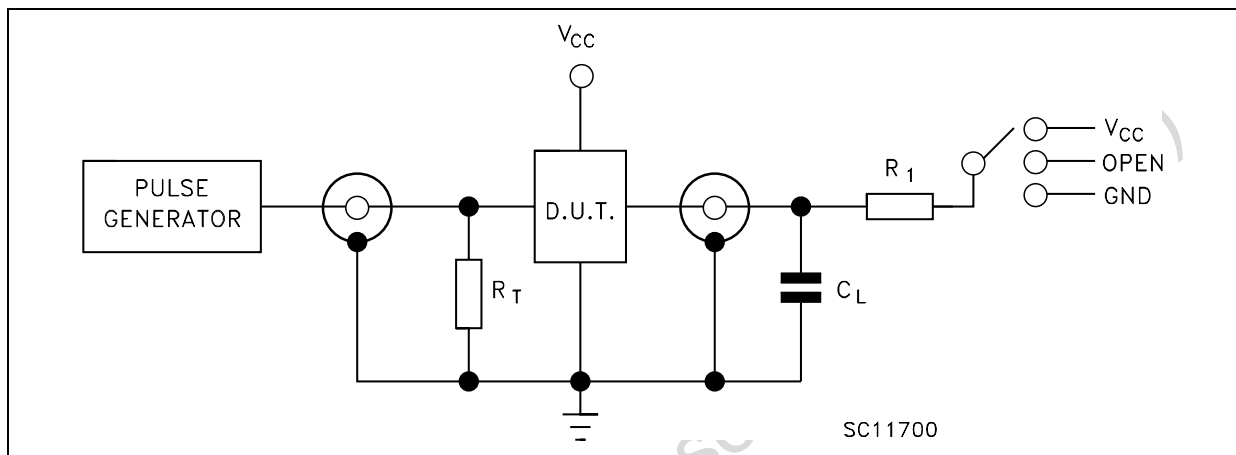
Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)	C _L (pF)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{TLH} t _{THL}	Output Transition Time	4.5	50		7	12		15		18	ns
t _{PLH} t _{PHL}	Propagation Delay Time	4.5	50		13	21		26		32	ns
		4.5	150		17	27		34		41	
t _{PZL} t _{PZH}	Output Enable Time	4.5	50	R _L = 1 KΩ	15	24		30		36	ns
		4.5	150		19	30		38		45	
t _{PLZ} t _{PHZ}	Output Disable Time	4.5	50	R _L = 1 KΩ	17	24		30		36	ns

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)				56						pF

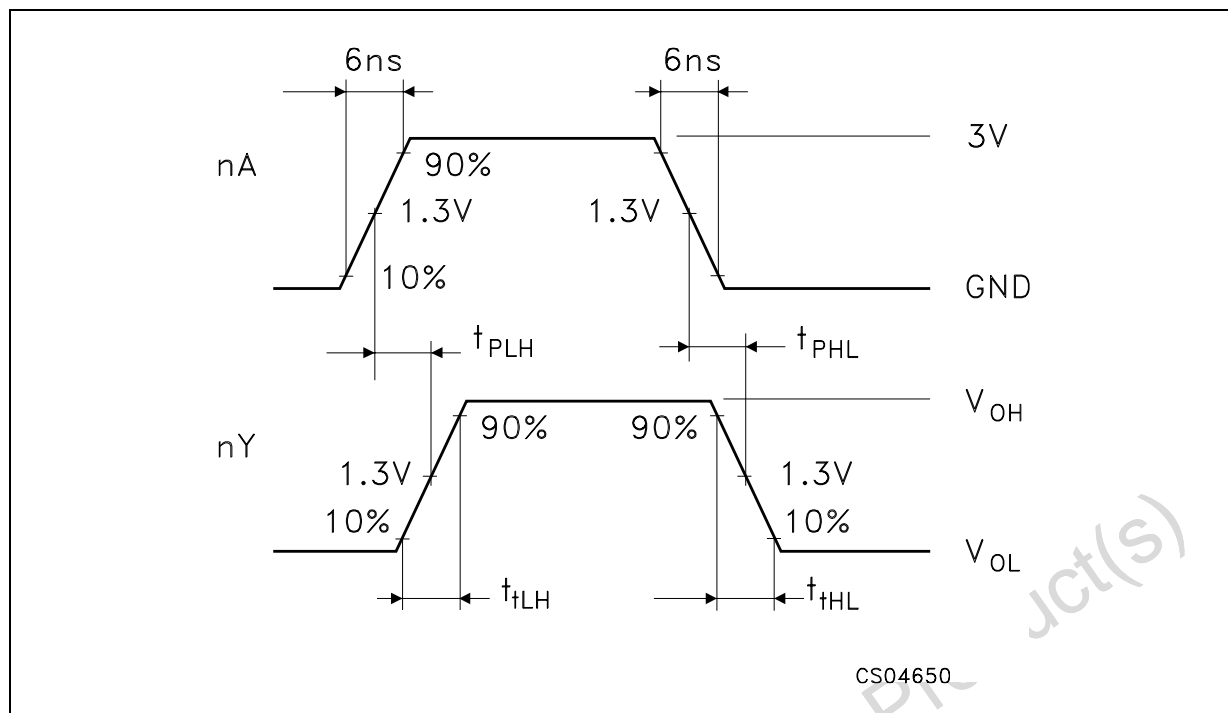
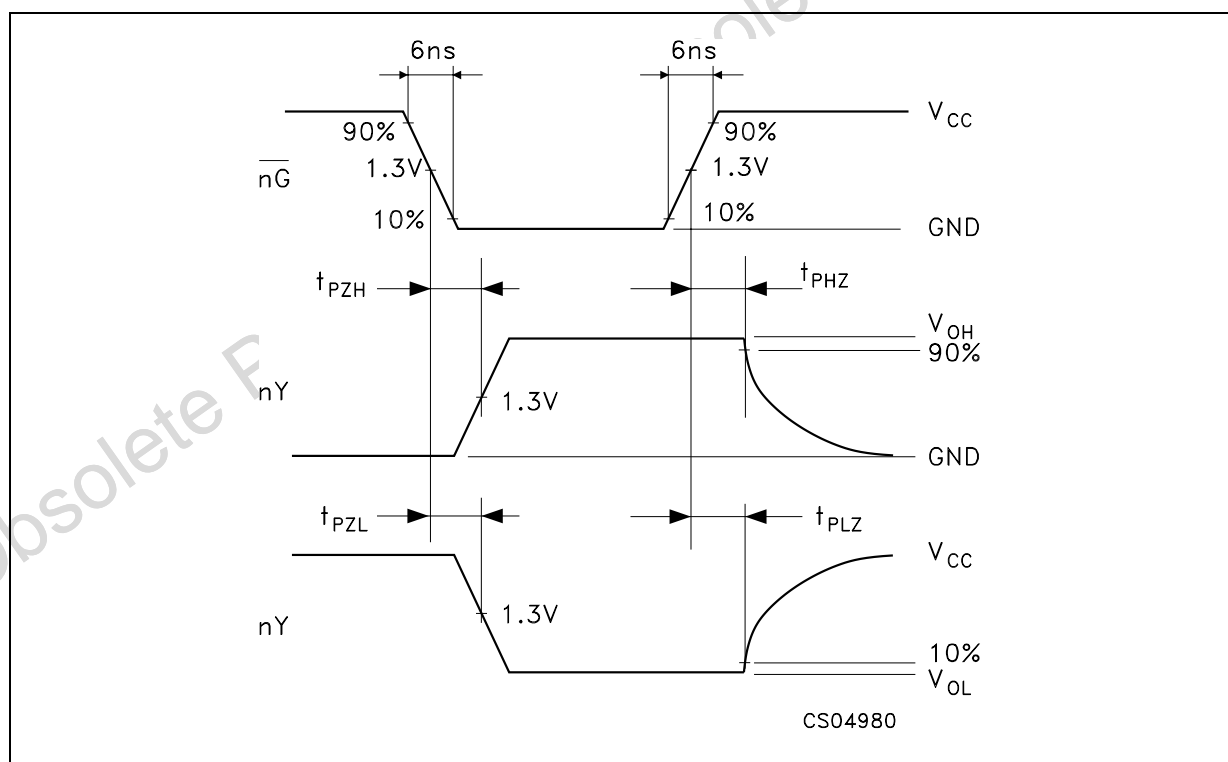
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT



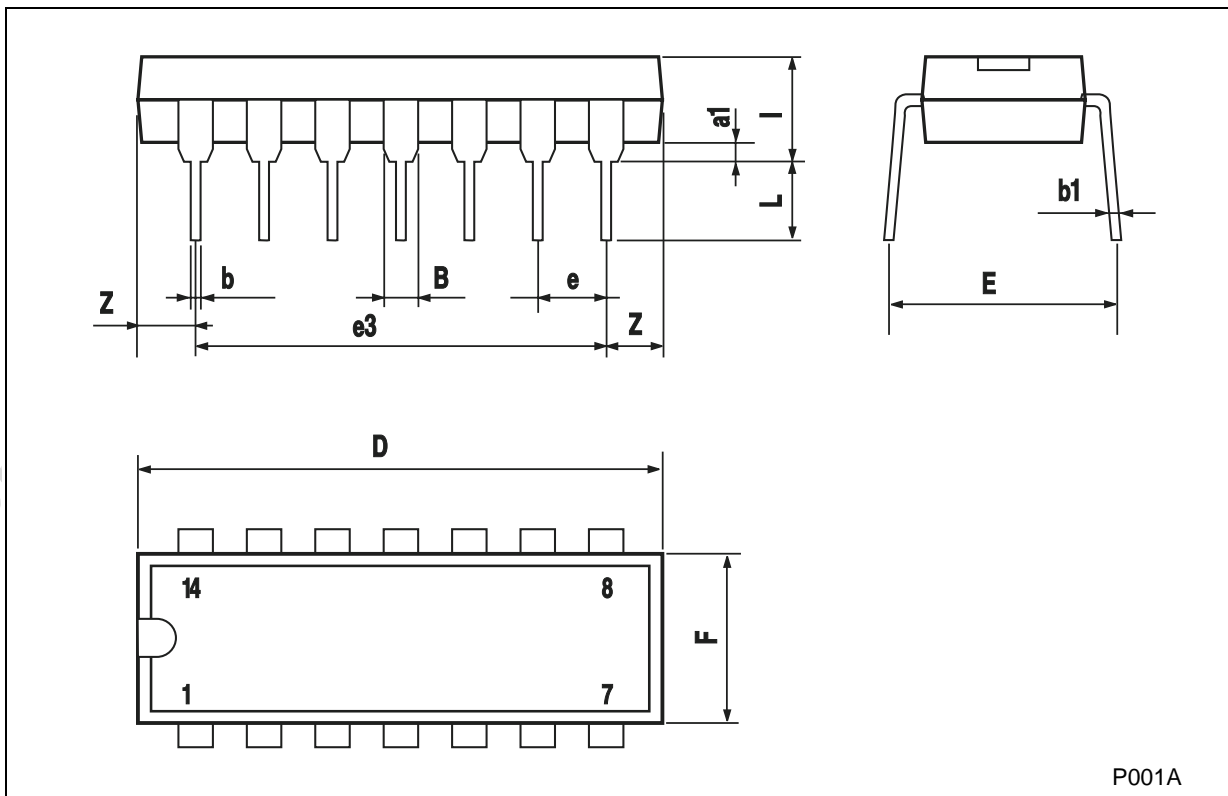
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	V _{CC}
t _{PZH} , t _{PHZ}	GND

C_L = 50pF/150pF or equivalent (includes jig and probe capacitance)
 R₁ = 1KΩ or equivalent
 R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1 : PROPAGATION DELAY TIMES ($f=1\text{MHz}$; 50% duty cycle)**WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIMES** ($f=1\text{MHz}$; 50% duty cycle)

Plastic DIP-14 MECHANICAL DATA

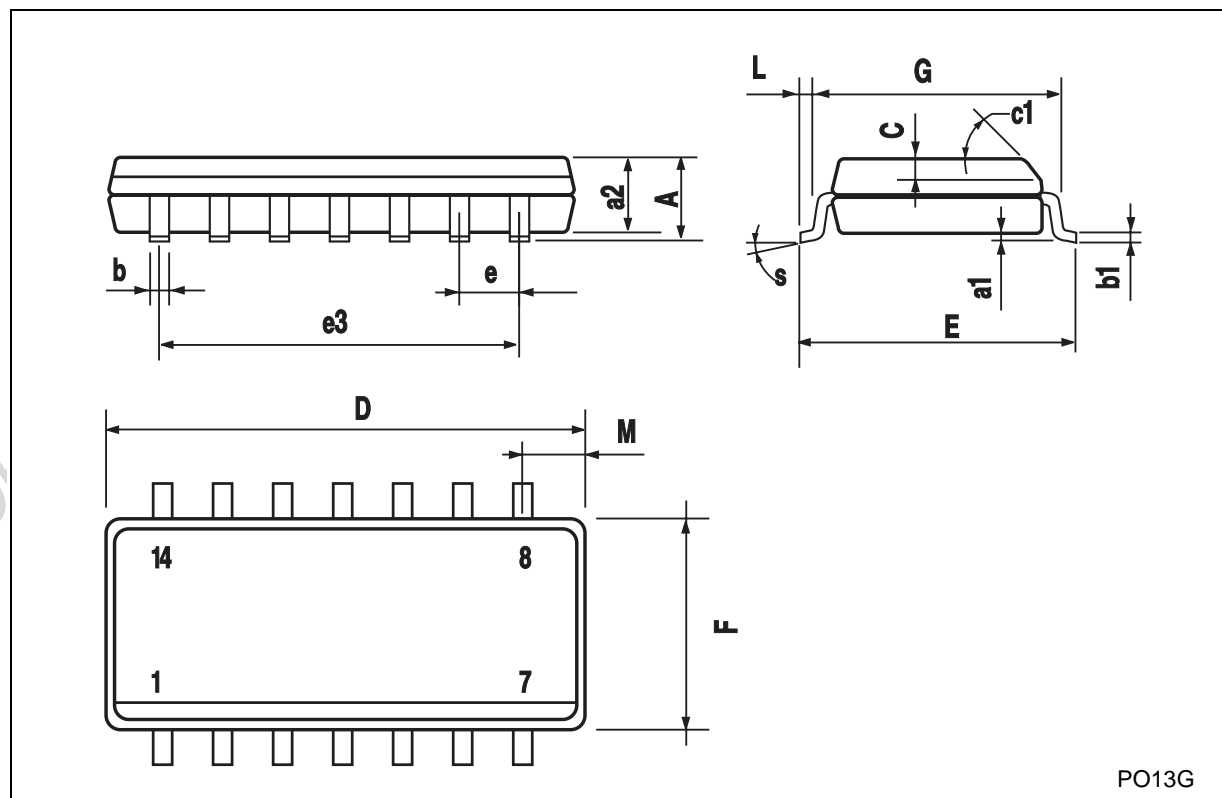
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

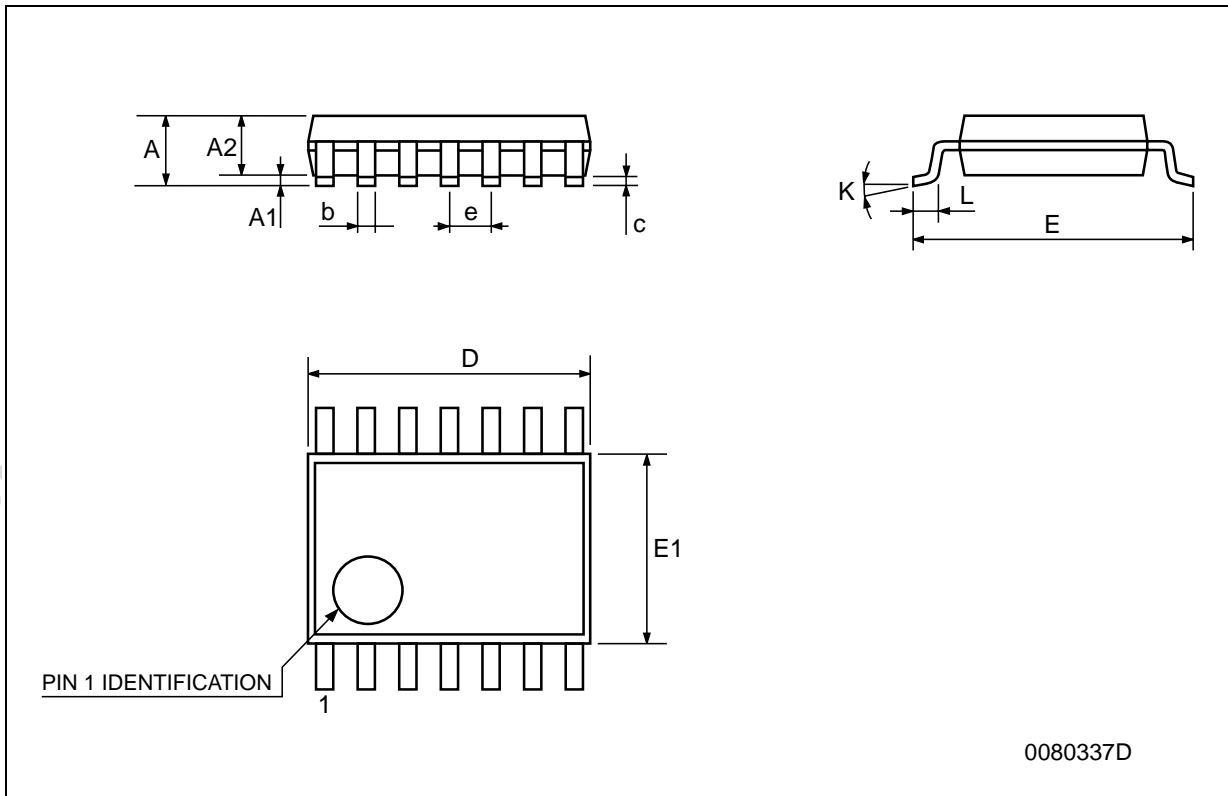
SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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